

Correspondence

Corrections to “On the Design and Optimization of Three-Terminal Light-Emitting Device in Silicon CMOS Technology”

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SINCE the publication of the paper [1], the author has discovered a number of errors. The following is a list of corrections.

- 1) In Fig. 1, the substrate orientation should read “<100> silicon”.
- 2) Fig. 10 and the related descriptions are wrong. The second paragraph following Fig. 10, which starts from “The frequency response of the MOS-capacitor modulator is measured using an ac signal generated by an opto-RF vector network analyzer (Agilent 86030 A),” should instead be replaced by the following:

“The optical power emitted from the reverse-biased p-n junctions in the wavelength range 400–900 nm is just few nanowatts. This prohibits to measure in a meaningful way the emitted power. However, since the actual speed is somewhat lower than the intrinsic speed, a maximum frequency of few tens of gigahertz could be estimated.”

REFERENCE

- [1] K. Xu, “On the design and optimization of three-terminal light-emitting device in silicon CMOS technology,” *IEEE J. Sel. Topics Quantum Electron.*, vol. 20, no. 4, p. 8201208, Jul./Aug. 2014.

Manuscript received April 2, 2014; revised April 9, 2014; accepted April 9, 2014. Date of publication April 21, 2014; date of current version May 13, 2014.

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Digital Object Identifier 10.1109/JSTQE.2014.2318271